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# Photo-controlled Organic Thin Film Transistors

## Using Soluble $\pi$ -Conjugated Molecules

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We fabricated highly photo-sensitive organic thin film transistors using soluble star-shaped molecules with four-armed  $\pi$ -conjugation paths, such as 4(HPBT)-benzene, 4(HP3T)-benzene, and 4(HPDTP)-benzene molecules having a relatively high quantum yield. The 4(HPBT)-benzene based organic photo-transistors (OPTs) exhibited high photo-sensitivity (2500 ~ 4300 A/W) even with low optical powers (6.8 ~ 30  $\mu$ W/cm<sup>2</sup>) at zero gate bias. The measured photo-sensitivity of the devices was much higher than that of inorganic single crystal Si based photo-transistors, as well as that of other OPTs reported earlier. With the highly photo-sensitive characteristics of the 4(HPBT)-benzene based OPTs, we observed the high ratio of on and off current switching as  $\sim 4 \times 10^4$  with low optical power and low gate bias. The slow relaxation of the photo-induced charges and charge trapping phenomena at the interface could lead to a reproducible memory operation for 4(HPBT)-benzene based OPTs. We also present the photo-enhanced memory effect using soluble TIPS-pentacene based OTFTs.